NSN 5961-01-235-3269

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View Online at https://aerobasegroup.com/nsn/5961-01-235-3269 **Inclosure Material:** Metal **Overall Length:** 0.210 inches **Terminal Length:** 0.750 inches **Overall Diameter:** 0.230 inches **Internal Configuration:** Field effect Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Gate **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case and quality assurance level s **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: -40.0 drain to gate voltage and 40.0 drain to source voltage and 40.0 gate to source voltage **Current Rating Per Characteristic:** 50.00 milliamperes gate current **Power Rating Per Characteristic:** 1.8 watts total power dissipation **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 3 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/385 government specification Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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